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BLL6G1214L-250

LDMOS L-band radar power transistor

AMPLEON

Rev. 3 — 28 January 2016

Product data sheet

1. Product profile

1.1 General description

250 W LDMOS power transistor intended for L-band radar applications in the 1.2 GHz to 1.4 GHz range.

Table 1. Test information

Typical RF performance at T_{case} = 25 °C; t_p = 1 ms; δ = 10 %; I_{Dq} = 150 mA; in a class-AB production test circuit.

Test signal	f	V _{DS}	P_L	G _p	η_{D}	t _r	t _f
	(GHz)	(V)	(W)	(dB)	(%)	(ns)	(ns)
pulsed RF	1.2 to 1.4	36	250	15	45	15	5

1.2 Features and benefits

- Easy power control
- Integrated ESD protection
- High flexibility with respect to pulse formats
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (1.2 GHz to 1.4 GHz)
- Internally matched for ease of use
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

 L-band power amplifiers for radar applications in the 1.2 GHz to 1.4 GHz frequency range

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	drain		_
2	gate		1
3	source		2
			3 sym112

^[1] Connected to flange

3. Ordering information

Table 3. Ordering information

Type number	Packag)		
	Name	Description	Version	
BLL6G1214L-250	-	flanged ceramic package; 2 mounting holes; 2 leads	SOT502A	

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	89	V
V_{GS}	gate-source voltage		-0.5	+11	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	200	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-case)}	thermal resistance from junction to case	T _{case} = 85 °C; P _L = 250 W	0.244	K/W
Z _{th(j-c)}	transient thermal impedance	$T_{case} = 85 ^{\circ}C; P_{L} = 250 W$ [1]		
	from junction to case	t_p = 1000 μ s; δ = 10 %	0.124	K/W
		t_p = 100 μ s; δ = 10 %	0.059	K/W
		t_p = 200 µs; δ = 10 %	0.077	K/W
		t_p = 300 µs; δ = 10 %	0.088	K/W
		t_p = 100 μ s; δ = 20 %	0.078	K/W

^[1] $Z_{th(j-c)}$ values are calculated from results obtained with ANSYS simulations and confirmed with IR measurements during development stage. During production: guaranteed by design.

6. Characteristics

Table 6. DC Characteristics

T_i = 25 ℃

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 3.36 \text{ mA}$	91.5	-	105.5	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 20 V; I _D = 336 mA	1.4	1.9	2.4	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 42 V	-	-	4.2	μА
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	50	59	-	Α
I_{GSS}	gate leakage current	$V_{GS} = 11 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	420	nA
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 336 mA	51.6	-	-	mS
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 11.7 \text{ A}$	_	-	127	mΩ

Table 7. AC Characteristics

 $T_i = 25 \, ^{\circ}$ C

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 40 \text{ V}; f = 1 \text{ MHz}$	-	285	-	pF
C _{oss}	output capacitance	V _{GS} = 0 V; V _{DS} = 40 V; f = 1 MHz	-	90	-	pF
C _{rss}	reverse transfer capacitance	V _{GS} = 0 V; V _{DS} = 40 V; f = 1 MHz	-	3	-	pF

Table 8. RF characteristics

Test signal: pulsed RF; t_p = 1 ms; δ = 10 %; RF performance at V_{DS} = 36 V; I_{Dq} = 150 mA; T_{case} = 25 °C; unless otherwise specified, in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
P_L	output power		250	-	-	W
f _{range}	frequency range		1200	-	1400	MHz
t _p	pulse duration	δ = 10 %	-	-	1	ms
		δ = 20 %	-	-	100	μS
η_{D}	drain efficiency		42	45	-	%
t _r	rise time	P _L = 250 W [1]	-	-	200	ns
t _f	fall time	P _L = 250 W [1]	-	-	200	ns
Gp	power gain		13	15	-	dB
P _{droop(pulse)}	pulse droop power		-	-	0.6	dB
RLin	input return loss		-	-	-7	dB

^[1] The rise and fall time of the input circuit will be 5 ns maximum.

7. Test information

7.1 Ruggedness in class-AB operation

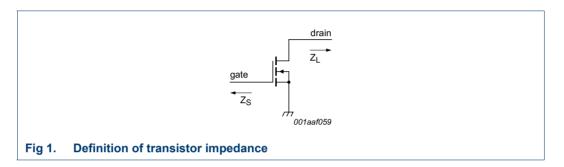
The BLL6G1214L-250 is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 36 V; I_{Dq} = 150 mA; P_{L} = 250 W; t_{p} = 1 ms; δ = 10 %.

7.2 Impedance information

Table 9. Typical impedance

Typical values unless otherwise specified.

f	Zs	Z _L
(GHz)	(Ω)	(Ω)
1.2	1.077 – j2.78	1.288 – j1.014
1.3	1.352 – j2.949	1.139 – j1.086
1.4	1.881 – j2.640	1.038 – j1.132



7.3 Circuit information

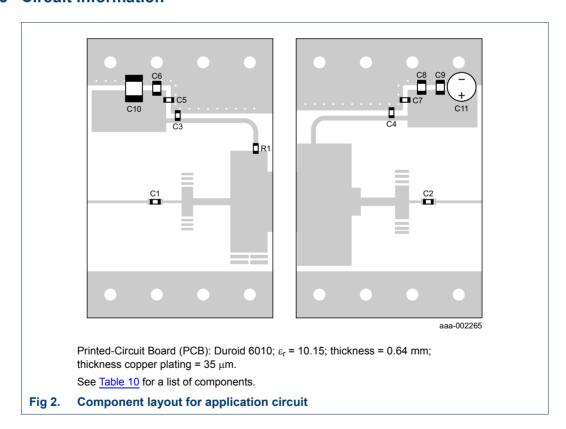


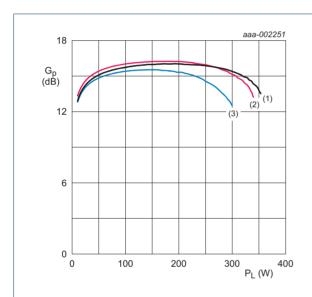
Table 10. List of components

For test circuit see Figure 2.

Component	Description	Value	Remarks
C1, C2, C3, C4, C7	multilayer ceramic chip capacitor	56 pF [1]	
C5, C8	multilayer ceramic chip capacitor	200 pF [2]	
C6, C9	multilayer ceramic chip capacitor	1 nF [3]	
C10	multilayer ceramic chip capacitor	10 μF, 20 V	
C11	electrolytic capacitor	22 μF, 63 V	
R1	resistor	10 Ω	SMD 0603

- [1] American Technical Ceramics type 100A or capacitor of same quality.
- [2] American Technical Ceramics type 100B or capacitor of same quality.
- [3] American Technical Ceramics type 700A or capacitor of same quality.

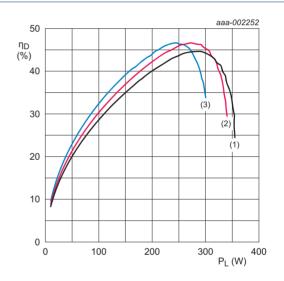
7.4 Graphical data



 t_p = 100 μ s; δ = 10 %; T_h = 25 °C.

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

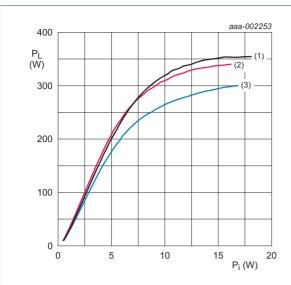
Fig 3. Power gain as a function of output power; typical values



 t_p = 100 μ s; δ = 10 %; T_h = 25 °C.

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

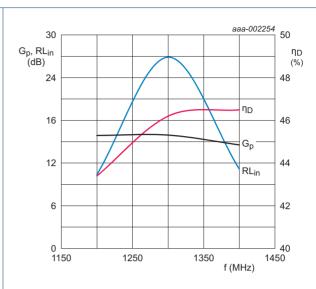
Fig 4. Drain efficiency as a function of output power; typical values



 t_{p} = 100 μ s; δ = 10 %; T_{h} = 25 °C.

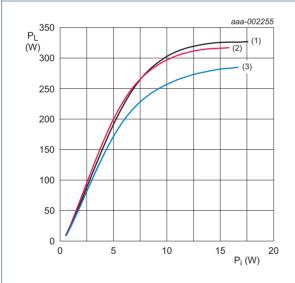
- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

Fig 5. Output power as a function of input power; typical values



 P_L = 250 W; t_p = 100 μ s; δ = 10 %; T_h = 25 °C.

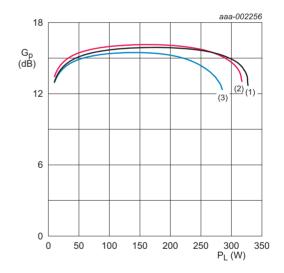
Fig 6. Power gain, input return loss and drain efficiency as function of frequency; typical values



 t_p = 1 ms; δ = 10 %; T_h = 25 °C.

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

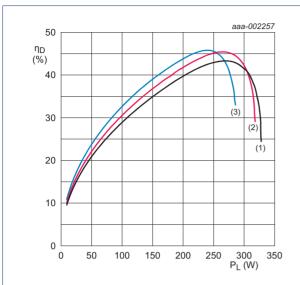
Fig 7. Output power as a function of input power; typical values



 t_p = 1 ms; δ = 10 %; T_h = 25 °C.

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

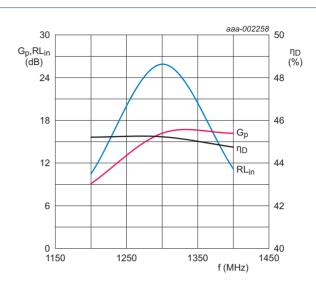
Fig 8. Power gain as a function of output power; typical values



 $t_p = 1 \text{ ms}; \delta = 10 \text{ %}; T_h = 25 \text{ °C}.$

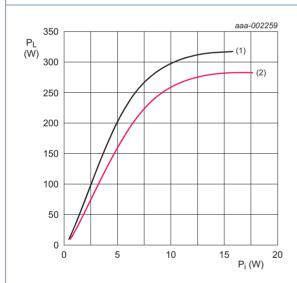
- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

Fig 9. Drain efficiency as a function of output power; typical values



 P_L = 250 W; t_p = 1 ms; δ = 10 %; T_h = 25 °C.

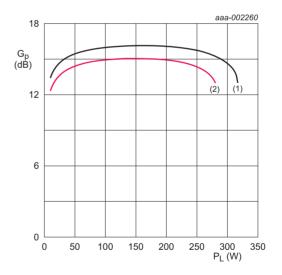
Fig 10. Power gain, input return loss and drain efficiency as function of frequency; typical values



f = 1300 MHz; $t_p = 1 \text{ ms}$; $\delta = 10 \%$.

- (1) T_h = 25 °C
- (2) $T_h = 85 \,^{\circ}C$

Fig 11. Output power as a function of input power; typical values

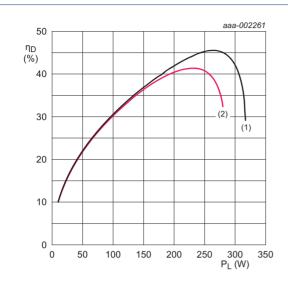


f = 1300 MHz; $t_p = 1 \text{ ms}$; $\delta = 10 \%$.

- (1) $T_h = 25 \, ^{\circ}C$
- (2) $T_h = 85 \, ^{\circ}C$

Fig 12. Power gain as a function of output power; typical values

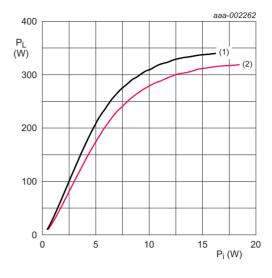
Product data sheet



 $f = 1300 \text{ MHz}; t_p = 1 \text{ ms}; \delta = 10 \%.$

- (1) T_h = 25 °C
- (2) $T_h = 85 \, ^{\circ}C$

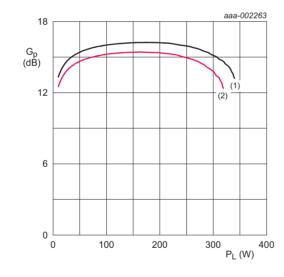
Fig 13. Drain efficiency as a function of output power; typical values



f = 1300 MHz; t_p = 100 μ s; δ = 10 %.

- (1) $T_h = 25 \, ^{\circ}C$
- (2) $T_h = 85 \, ^{\circ}C$

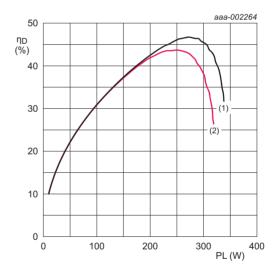
Fig 14. Output power as a function of input power; typical values



f = 1300 MHz; $t_p = 1 \text{ ms}$; $\delta = 10 \%$.

- (1) T_h = 25 °C
- (2) $T_h = 85 \,^{\circ}C$

Fig 15. Power gain as a function of output power; typical values



f = 1300 MHz; t_0 = 100 μ s; δ = 10 %.

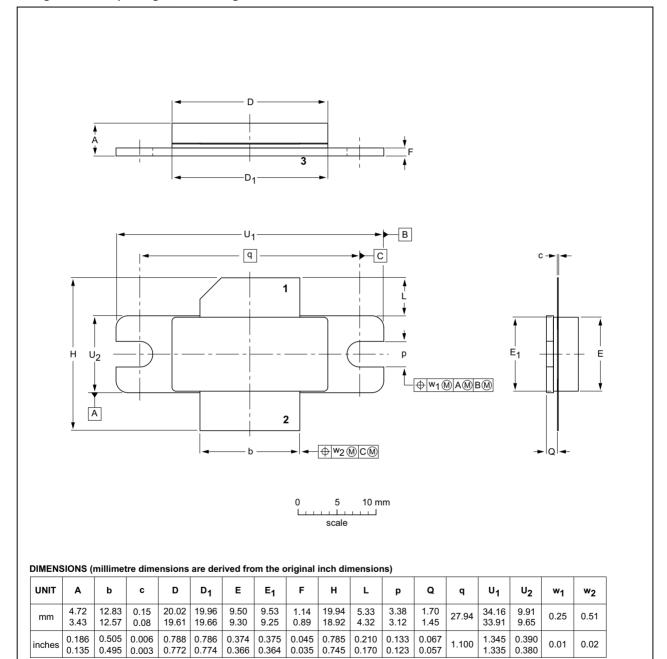
- (1) $T_h = 25 \, ^{\circ}C$
- (2) $T_h = 85 \, ^{\circ}C$

Fig 16. Drain efficiency as a function of output power; typical values

8. Package outline

Flanged ceramic package; 2 mounting holes; 2 leads

SOT502A



OUTLINE		REFER	RENCES	EUROPEAN	ICCUIT DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT502A					-03-01-10- 12-05-02	

Fig 17. Package outline SOT502A

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

10. Abbreviations

Table 11. Abbreviations

Acronym	Description
ESD	ElectroStatic Discharge
IR	InfraRed
L-band	Long wave band
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
SMD	Surface Mounted Device
VSWR	Voltage Standing-Wave Ratio

11. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLL6G1214L-250 v.3	20160128	Product data sheet	-	BLL6G1214L-250_ 1214LS-250 v.2
Modifications	 The document now describes only the eared version of this product: BLL6G1214L-250 			
BLL6G1214L-250_1214LS-250 v.2	20130624	Product data sheet	-	BLL6G1214L-250 v.1
BLL6G1214L-250 v.1	20120216	Preliminary data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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LDMOS L-band radar power transistor

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BLL6G1214L-250

LDMOS L-band radar power transistor

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